

IN THE CLAIMS:

Please add the following new claims:

23. A method of fabricating a semiconductor device, comprising the steps of:

providing a substrate having a doped semiconductor region, a gate wiring, a lower conductor structure, and an insulating layer overlying said lower structure and having at least ^{one} through opening extending to said lower conductor structure; and

forming an upper conductor structure on the insulating layer and causing the ^{upper} ~~lower~~ conductor structure to be connected to the lower conductor structure via the through opening;

wherein said step of forming an upper conductor structure is carried out by:

forming at least one layer of a metal, a metal silicide, a metal nitride, a metal carbide, or a conductive film; and

performing a plating operation in order to form a metal plating layer on the at least one layer, so that the metal plating layer adheres to the at least one layer.

24. A semiconductor device comprising:

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a substrate having ^a~~a~~ doped semiconductor region, a gate wiring, a lower conductor structure, an insulating layer overlying said lower structure and having at least one through opening extending to said lower conductor structure, and an upper conductor structure connected to said lower conductor structure via said through opening, wherein said upper ^{conductor} structure is formed by the steps of:

10 forming at least one layer of a metal, a metal silicide, a metal nitride, a metal carbide or a conductive oxide film on the insulating layer; and

performing a plating operation in order to form a metal plating layer on the at least one layer, so that
15 the metal plating layer adheres to the at least one layer. *TA*
